

**Features:**

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Inverter
- Inductive heating
- Chopper

V_{DSM}, V_{RSM}	V_{DRM}, V_{RRM}	Type & Outline
700V	600V	MKx200-06-413F3D
900V	800V	MKx200-08-413F3D
1100V	1000V	MKx200-10-413F3D
1300V	1200V	MKx200-12-413F3D
1500V	1400V	MKx200-14-413F3D
1700V	1600V	MKx200-16-413F3D

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^{\circ}\text{C}$	115			200	A
$I_{T(RMS)}$	RMS on-state current					314	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	115			50	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=60\%V_{RRM}$	115			4.8	kA
I^2t	I^2t for fusing coordination					115	$\text{A}^2\text{s} \times 10^3$
V_{TO}	Threshold voltage		115			0.90	V
r_T	On-state slope resistance					1.15	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=600\text{A}$	25			2.65	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	115			800	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	115			200	$\text{A}/\mu\text{s}$
t_q	Circuit commutated turn-off time	$I_{TM}=200\text{A}, t_p=1000\mu\text{s}, V_R=50\text{V}$ $dv/dt=30\text{V}/\mu\text{s}, di/dt=-20\text{A}/\mu\text{s}$	115	15		35	μs
t_{rr}	Reverse recovery time	$I_{FM}=200\text{A}, t_p=1000\mu\text{s}, -di/dt=20\text{A}/\mu\text{s}, V_R=50\text{V}$	115		3.0		μs
I_{GT}	Gate trigger current	$V_A=12\text{V}, I_A=1\text{A}$	25	30		200	mA
V_{GT}	Gate trigger voltage			1.0		2.5	V
I_H	Holding current			20		200	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	115	0.2			V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.100	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.040	$^{\circ}\text{C}/\text{W}$
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1\text{min}, I_{iso}=1\text{mA}(\text{MAX})$		2500			V
F_m	Terminal connection torque(M8)				12.0		N·m
	Mounting torque(M6)				6.0		N·m
T_{vj}	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				810		g
Outline				413F3D			

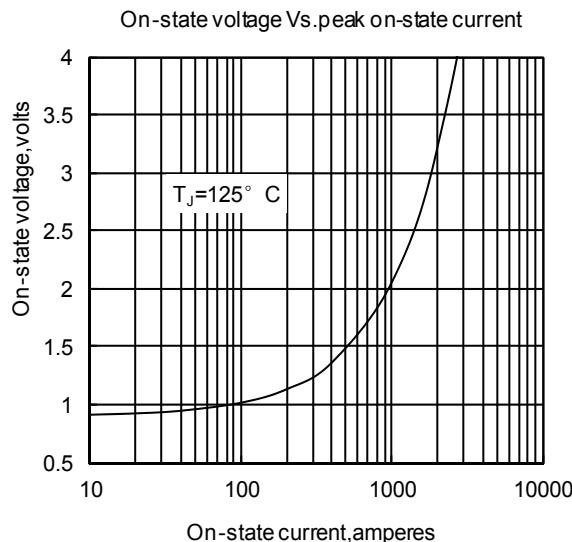


Fig1

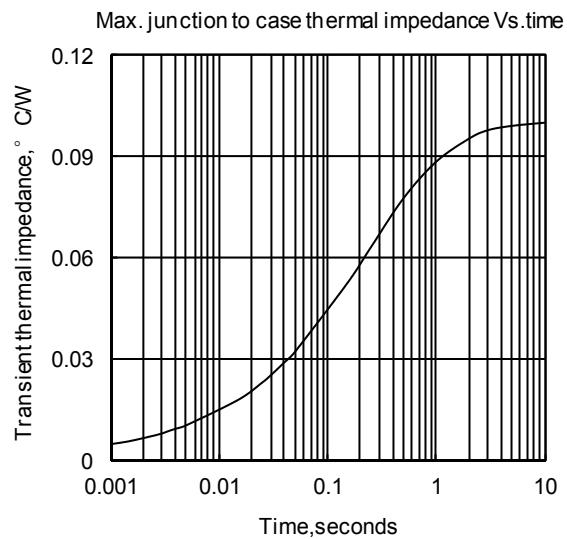


Fig2

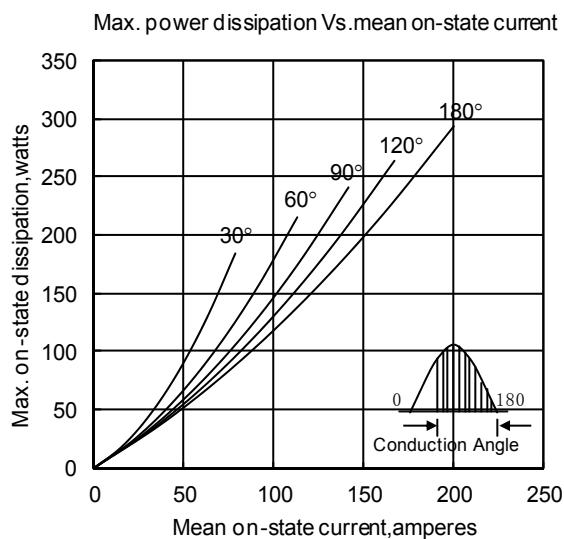


Fig3

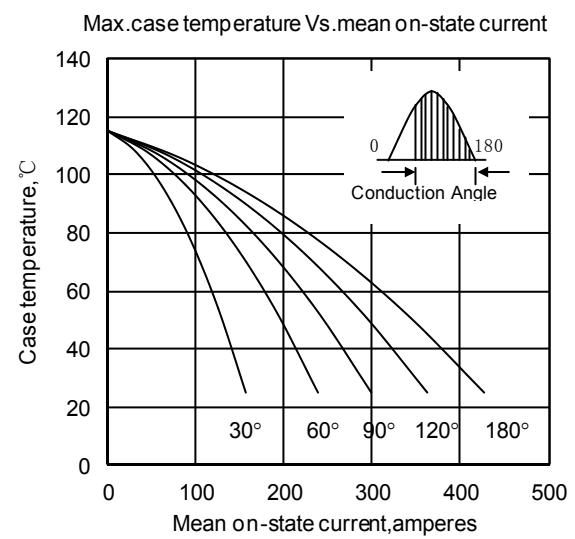


Fig4

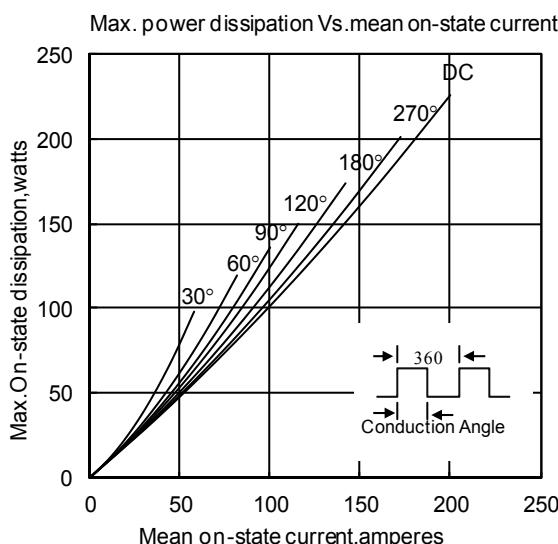


Fig5

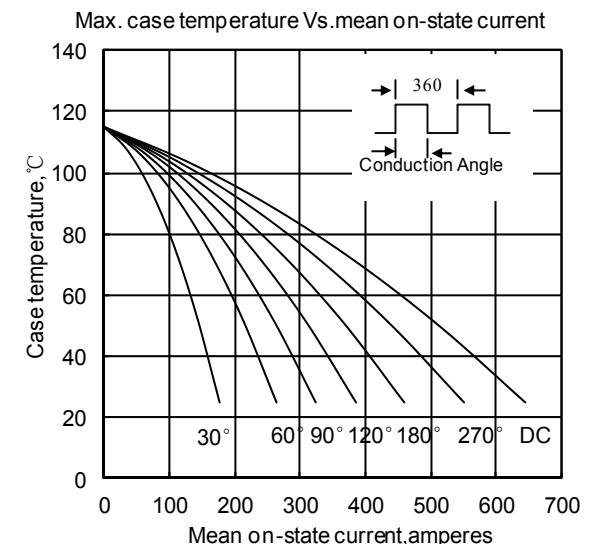


Fig6

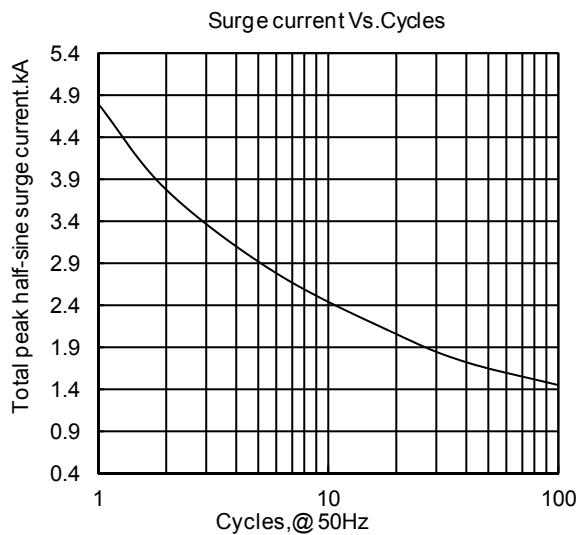


Fig7

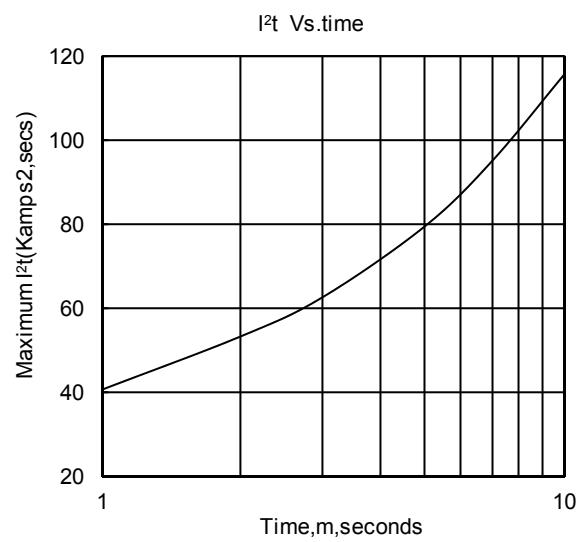


Fig8

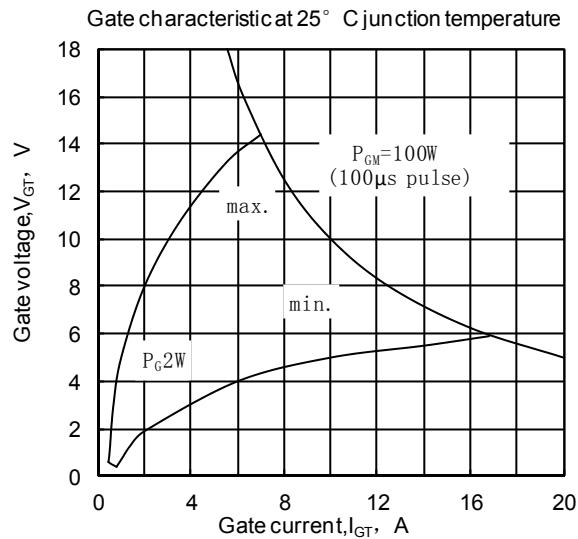


Fig9

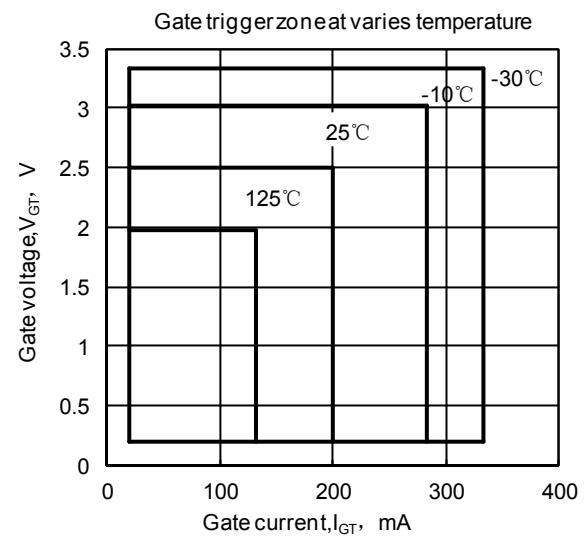
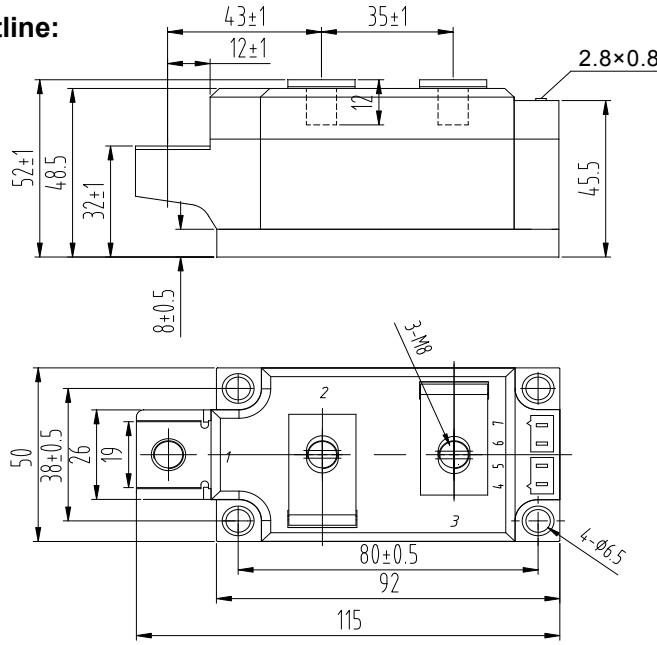


Fig10

Outline:

MKC

MKA

MKK

